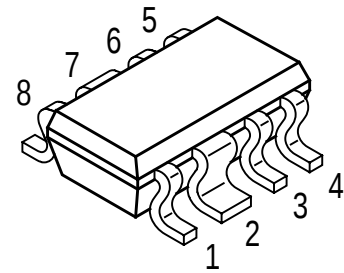


Self-Biased BFP420

- SIEGET[®]25- Technology
- Small SCT598-Package
- Control Pin For Switching The Device Off
- Current Easy Adjustable By An External Resistor
- Voltage Independent Current (2V – 4.5V)

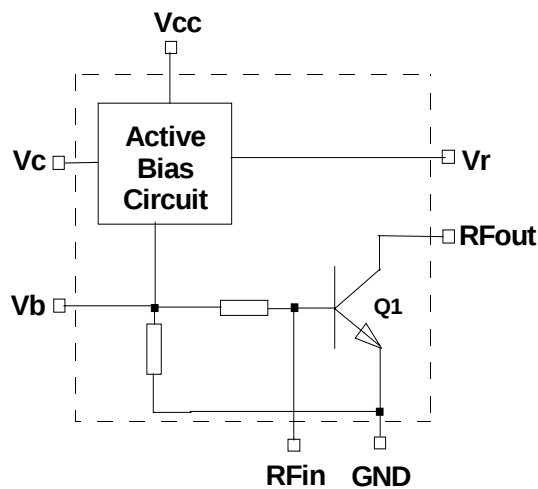


VPW05982

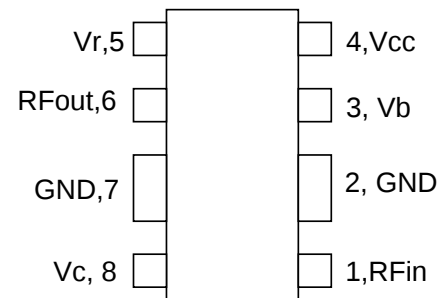
ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code (8-mm taped)	Pin Configuration (circuit Diagram)	Package
BGC420	42s	Q62702-G0092	see below	SCT598

Equivalent Circuit



Pin Connections, SCT598



Note: Top View

Description

The BGC420 is a silicon self biased RF Transistor (Q1). It offers an adjustable collector current nearly independent from device voltage in the range from 2.0V to 4.5V. Additionally a control pin (Vc) for switching the device off is provided. The collector current can be adjusted by connecting a resistor (Rx) between Vcc and Vr.

Maximum Ratings

Parameter	Symbol		Unit
Device current	I_{CC}	15	mA
Device voltage	V_{CC}	4.5	V
Total power dissipation, $T_s \leq 110^\circ\text{C}$ ¹⁾	P_{tot}	68	mW
Control voltage	V_C	$V_{CC}+0.5$	V
Input Current for pin 1	I_r	380	μA
Junction temperature	T_j	150	$^\circ\text{C}$
Ambient temperature range	T_A	-65...+150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-65...+150	$^\circ\text{C}$

Thermal Resistance

Junction-soldering point ¹⁾	$R_{th JS}$	≤ 270	K/W
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¹⁾ T_S is measured on the Ground lead at the soldering point to the pcb.

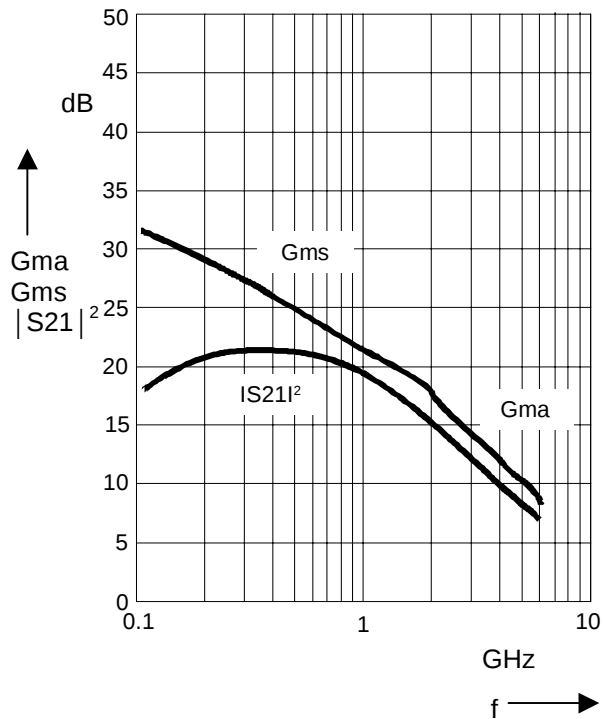
Electrical Specifications (Measured in Test Fixture applying the circuit specified in Figure 1 with $R_x=82\Omega$), $T_c=25^\circ\text{C}$, $V_{CC}=3\text{V}$, $I_{CC}\approx 7\text{mA}$ unless noted

Symbol	Parameter	Unit	Min	Typ	Max
G_p	Power Gain ($ S_{21} ^2$)	f=900MHz	17.5	19	
		f=1.8GHz	14.5	16	
NF	Noise Figure (in 50 Ω System)	f=900MHz		1.3	1.5
		f=1.8GHz		1.5	1.7
P_{-1dB}	Output Power at 1dB Gain Compression (in 50 Ω System)	f=900MHz		1	
		f=1.8GHz		1	
IP_3	Third Order Intercept Point (Output, Γ_{Opt})	f=900MHz		15	
		f=1.8GHz		15	
RL_{in}	Input Return Loss	f=900MHz		7	
		f=1.8GHz		9	
RL_{out}	Output Return Loss	f=900MHz		4	
		f=1.8GHz		7	
t_{on}	On Switching Time ³⁾	μs		3.7	
t_{off}	Off Switching Time ³⁾	μs		2.5	
I_{leak}	Leakage Current In Sleep Mode	μA		<10	
I_{VcOn}	Controll Pin (V_C) Current in Active Mode ²⁾	μA		35	
I_{VcOff}	Controll Pin (V_C) Current in Sleep Mode ²⁾	nA		-60	
V_{cmin}	Minimum Voltage at V_C for Sleep Mode	V		$V_{CC} - 0.3\text{V}$	
V_{cmax}	Maximum Voltage at V_C for Active Mode	V		$0\text{V}+0.3\text{V}$	

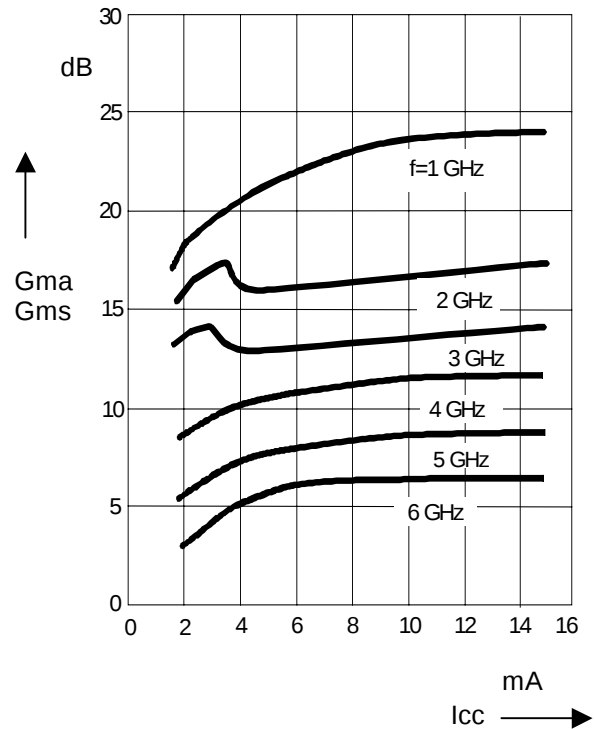
²⁾ A positive sign denotes a current flowing form the Pin into the external circuit.

³⁾ This values are valid for $C_2=1\text{nF}$, $C_3=100\text{pF}$ and 220pF Coupling capacitors at R_{Fin} and R_{Fout} .

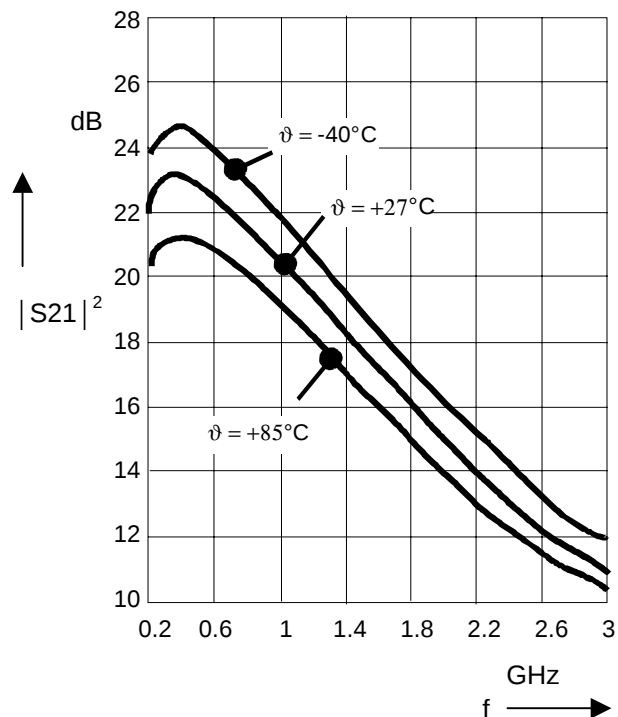
**Power Gain
versus Frequency**
 $V_{CC}=3V$, $I_{CC}=5mA$



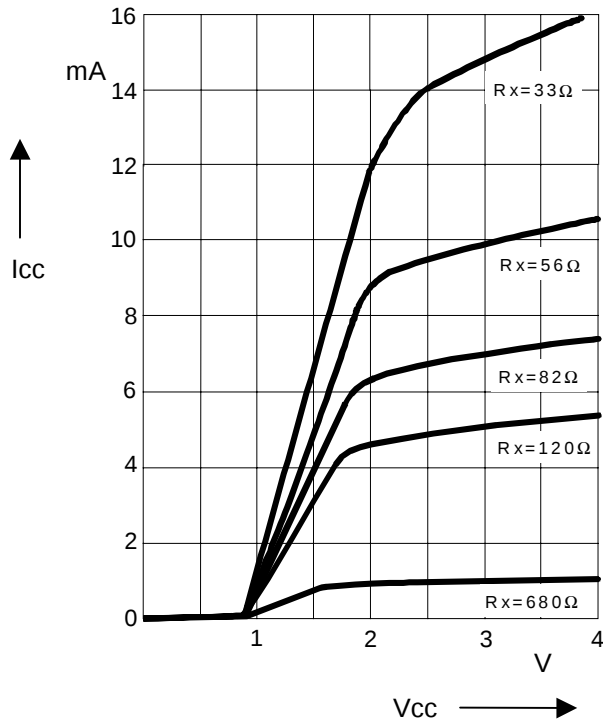
**Power Gain
versus Device Current**
 $V_{CC}=3V$



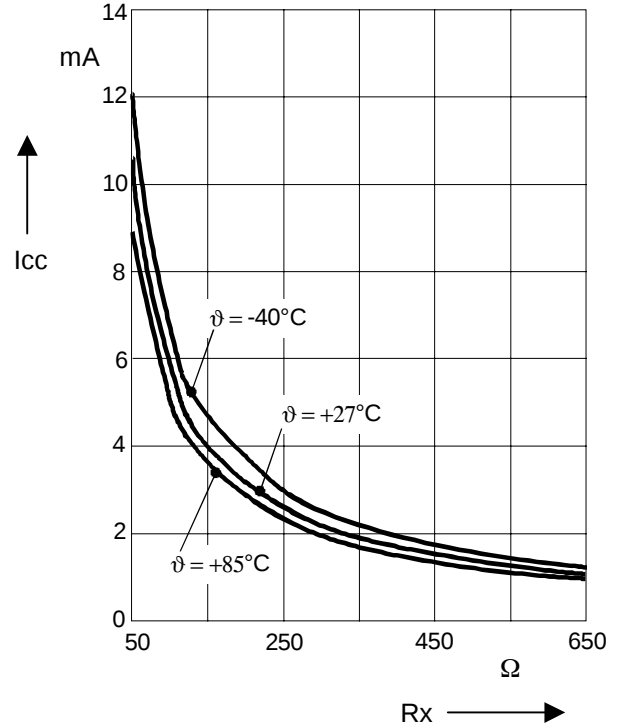
**$|S_{21}|^2$
versus Frequency and Temperature**
 $V_{CC}=3V$, $I_{CC}=7mA$



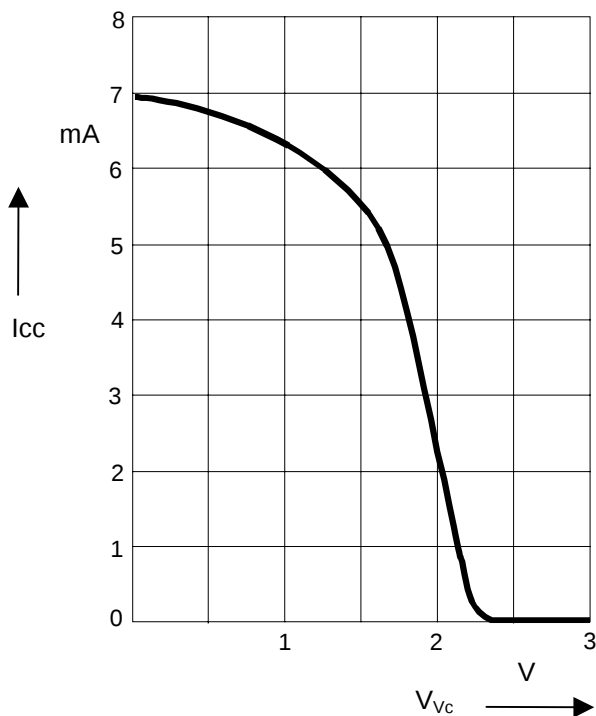
**Device Current
versus Device Voltage**



**Device Current
versus R_x and Temperature
 $V_{CC}=3V$**



**Device Current
versus Voltage at V_C
 $V_{CC}=3V$; $R_x=82\Omega$**



Typical Application

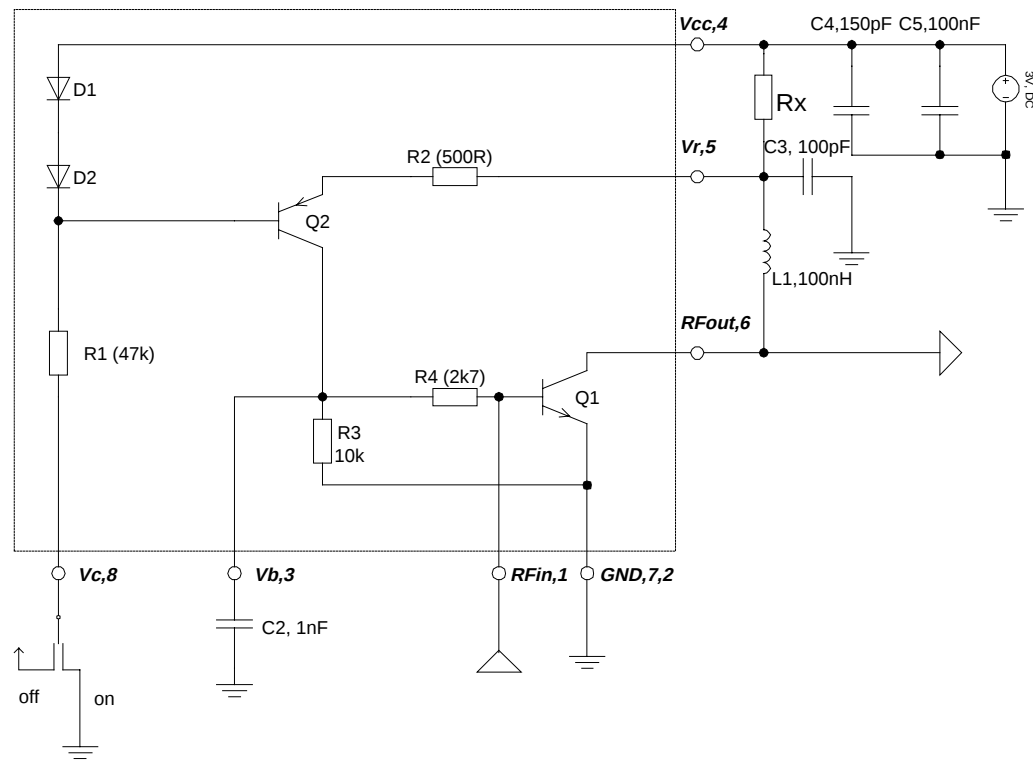


Figure 1. Typical Application and Internal Circuit

Remarks:

- 1) To provide low frequency stability C2 should be 10 times C3.
- 2) Be aware that also coupling capacitors determine the switching times.
- 3) The collector current at Q1 can be estimated by $I_c = 0.6V / R_x[\Omega]$.
- 4) Place C2 as close to the device as possible.

Layout Proposal

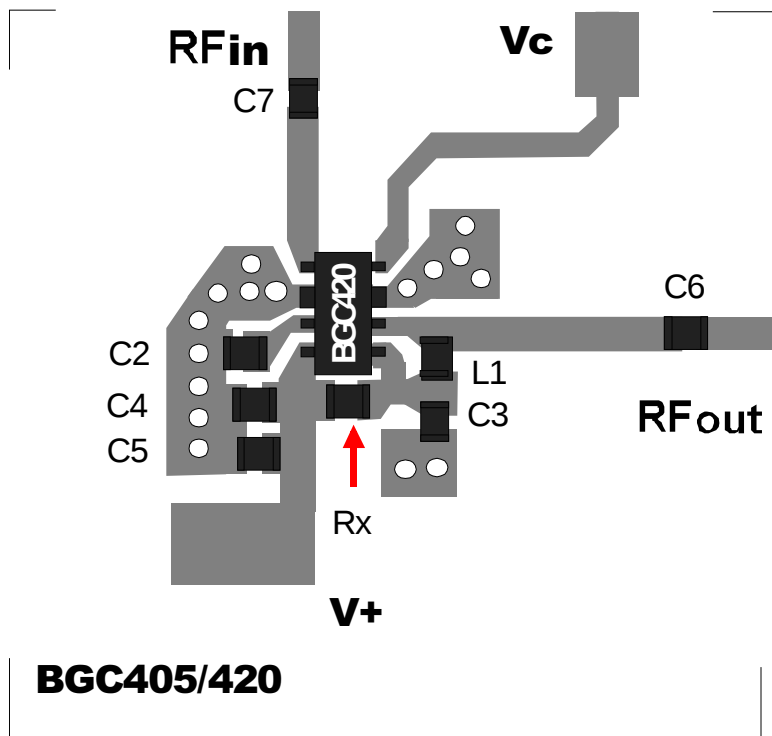


Figure 2. Layout Proposal

Part List for $V_{CC}=3V$, $I_{CC}\approx 7mA$

Component	Value	Comment
L1	100nH	RFC
C2	1nF	Compensation Capacitor for Low Frequency Stabilization
C3	100pF	RFC
C4	150pF	Blocking Capacitor
C5	100nF	Blocking Capacitor
C6	220pF	Coupling Capacitor
C7	220pF	Coupling Capacitor
Rx	82Ω	Current Adjust
Substrate	h=0.5mm	Fr4, $\epsilon_r=4.5$
BGC420		

This proposal demonstrates how to use the BGC420 as a *Self-Biased Transistor*. As for a discrete Transistor matching circuits have to be applied. A good starting point for various applications are the Application Notes provided for the BFP420.

SPICE Model

The following SPICE Listing describes the circuit shown in figure 3. It is valid for low frequencies. For frequencies above 100MHz the parasitic circuit elements noted in figure 4 and table 1 should be added.

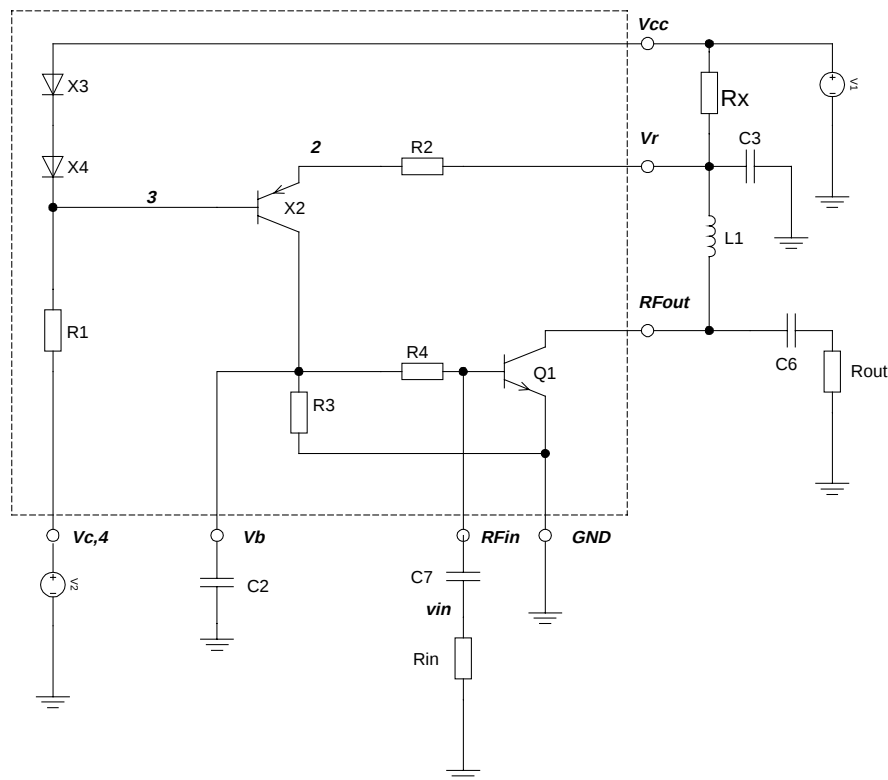


Figure. 3: Circuit used in the SPICE File

```
* Preliminary SPICE Model for BGC420 (valid for frequencies below 100MHz)
* SIEMENS HIGH FREQUENCY PRODUCTS
* Small Scale MMIC Design Group

.PARAM R=82

** Analysis setup **
*.TRAN 2ns 15u 0 2n
.TEMP +27
.DC LIN V1 0V 4V 0.1V
*.DC LIN V2 0V 3V 0.1V
.STEP PARAM R LIST 56 82 120 680

* Voltage supply
V1 Vcc 0 DC 3.0V
V2 Vc 0 DC 0.0V
*Vpul Vc 0 PULSE(0 3V 100ns 0 0 9us 1000m)
```

* Internal Resistors

```
R1 3 Vc 47k TC=-0.0006,0.0000025
R2 Vr 2 500 TC=-0.0006,0.0
R3 Vb 0 10k TC=-0.0006,0.0000025
R4 Vb rfin 2.7k TC=-0.0006,0.0
```

* External Resistors

```
Rx Vcc Vr {R} TC=+0.000050,0.0
Rout vout 0 50
Rin vin 0 50
```

* External Capacitors

```
C2 Vb 0 1nF
C3 Vr 0 100pF
C7 rfin vin 220pF
C6 rfout vout 220pF
```

* Inductors (external)

```
L1 Vr rfout 100nH
```

* Transistors

```
Q1 rfout rfin 0 BFP420
X2 2 3 Vb 0 8PL18
X3 Vcc 5 5 0 2PL18
X4 5 3 3 0 2PL18
```

.PROBE

.MODEL BFP420 NPN(

+ IS = 2.0045e-16	BF = 72.534	NF = 1.2432
+ VAF = 28.383	IKF = 0.48731	ISE = 1.9049e-14
+ NE = 2.0518	BR = 7.8287	NR = 1.3325
+ VAR = 19.705	IKR = 0.69141	ISC = 1.9237e-17
+ NC = 1.1724	RB = 3.4849	IRB = 0.00072983
+ RBM = 8.5757	RE = 0.31111	RC = 0.10105
+ CJE = 1.8063e-15	VJE = 0.8051	MJE = 0.46576
+ TF = 6.7661e-12	XTF = 0.42199	VTF = 0.23794
+ ITF = 0.001	PTF = 0	CJC = 2.3453e-13
+ VJC = 0.81969	MJC = 0.30232	XCJC = 0.3
+ TR = 2.3249e-09	CJS = 0	VJS = 0.75
+ MJS = 0	XTB = 0	EG = 1.11
+ XTI = 3	FC = 0.73234)	

* PNP: PL18 E B C Bulk

.SUBCKT 8PL18 3 2 1 94

```
Q1 993 2 3 94 TL18 8
Q2 94 2 3 94 VSL18 8
Q3 94 2 993 94 LSL18 8
RCEX 993 1 0.204
.ENDS
```

.SUBCKT 2PL18 3 2 1 94

```
Q1 993 2 3 94 TL18 2
Q2 94 2 3 94 VSL18 2
Q3 94 2 993 94 LSL18 2
RCEX 993 1 0.816
.ENDS
```

.MODEL	TL18	PNP			
+IS	= 2.914E-17	NF	= 1.000E+00	BF	= 4.005E+02
+NE	= 1.553E+00	ISE	= 6.923E-16	NR	= 1.000E+00
+BR	= 2.869E+01	NC	= 1.500E+00	ISC	= 8.190E-15
+VAF	= 6.000E+01	IKF	= 1.676E-04	VAR	= 2.214E+00
+IKR	= 2.474E-05	RB	= 6.000E+01	IRB	= 0.000E+00
+RBM	= 4.000E+01	RE	= 2.597E+00	RC	= 4.000E+00
+XTB	= -6.000E-01	EG	= 1.156E+00	XTI	= 3.000E+00
+CJE	= 1.200E-14	VJE	= 4.900E-01	MJE	= 1.360E-01
+TF	= 7.600E-10	XTF	= 2.872E-01	VTF	= 1.000E+03
+ITF	= 1.400E-02	CJC	= 4.700E-13	VJC	= 7.610E-01
+MJC	= 3.760E-01	XCJC	= 1.000E+00	TR	= 0.000E+00
+CJS	= 0.000E+00	VJS	= 7.500E-01	MJS	= 0.000E+00
+PTF	= 0.000E+00	FC	= 5.000E-01		

.MODEL	VSL18	PNP			
+IS	= 1.630E-19	NF	= 1.000E+00	BF	= 1.000E+09
+NE	= 1.500E+00	ISE	= 0.000E+00	NR	= 1.000E+00
+BR	= 1.000E+09	NC	= 2.000E+00	ISC	= 0.000E+00
+VAF	= 1.000E+02	IKF	= 1.794E-04	VAR	= 1.700E+00
+IKR	= 1.000E+00	RB	= 0.000E+00	IRB	= 0.000E+00
+RBM	= 0.000E+00	RE	= 0.000E+00	RC	= 0.000E+00
+XTB	= 0.000E+00	EG	= 1.122E+00	XTI	= 3.000E+00
+CJE	= 0.000E+00	VJE	= 6.800E-01	MJE	= 3.400E-01
+TF	= 2.000E-09	XTF	= 0.000E+00	VTF	= 1.000E+03
+ITF	= 1.000E+06	CJC	= 1.950E-13	VJC	= 5.500E-01
+MJC	= 3.770E-01	XCJC	= 0.000E+00	TR	= 0.000E+00
+CJS	= 0.000E+00	VJS	= 7.500E-01	MJS	= 0.000E+00
+PTF	= 0.000E+00	FC	= 5.000E-01		

.MODEL	LSL18	PNP			
+IS	= 4.261E-17	NF	= 1.000E+00	BF	= 1.000E+09
+NE	= 1.500E+00	ISE	= 0.000E+00	NR	= 1.000E+00
+BR	= 1.000E+09	NC	= 2.000E+00	ISC	= 0.000E+00
+VAF	= 6.000E+01	IKF	= 9.648E-05	VAR	= 1.700E+00
+IKR	= 1.000E+00	RB	= 0.000E+00	IRB	= 0.000E+00
+RBM	= 0.000E+00	RE	= 0.000E+00	RC	= 0.000E+00
+XTB	= 0.000E+00	EG	= 1.158E+00	XTI	= 3.000E+00
+CJE	= 0.000E+00	VJE	= 6.800E-01	MJE	= 3.400E-01
+TF	= 1.000E-09	XTF	= 0.000E+00	VTF	= 1.000E+03
+ITF	= 1.000E+06	CJC	= 0.000E+00	VJC	= 4.600E-01
+MJC	= 3.000E-01	XCJC	= 0.000E+00	TR	= 0.000E+00
+CJS	= 0.000E+00	VJS	= 7.500E-01	MJS	= 0.000E+00
+PTF	= 0.000E+00	FC	= 5.000E-01		

.END

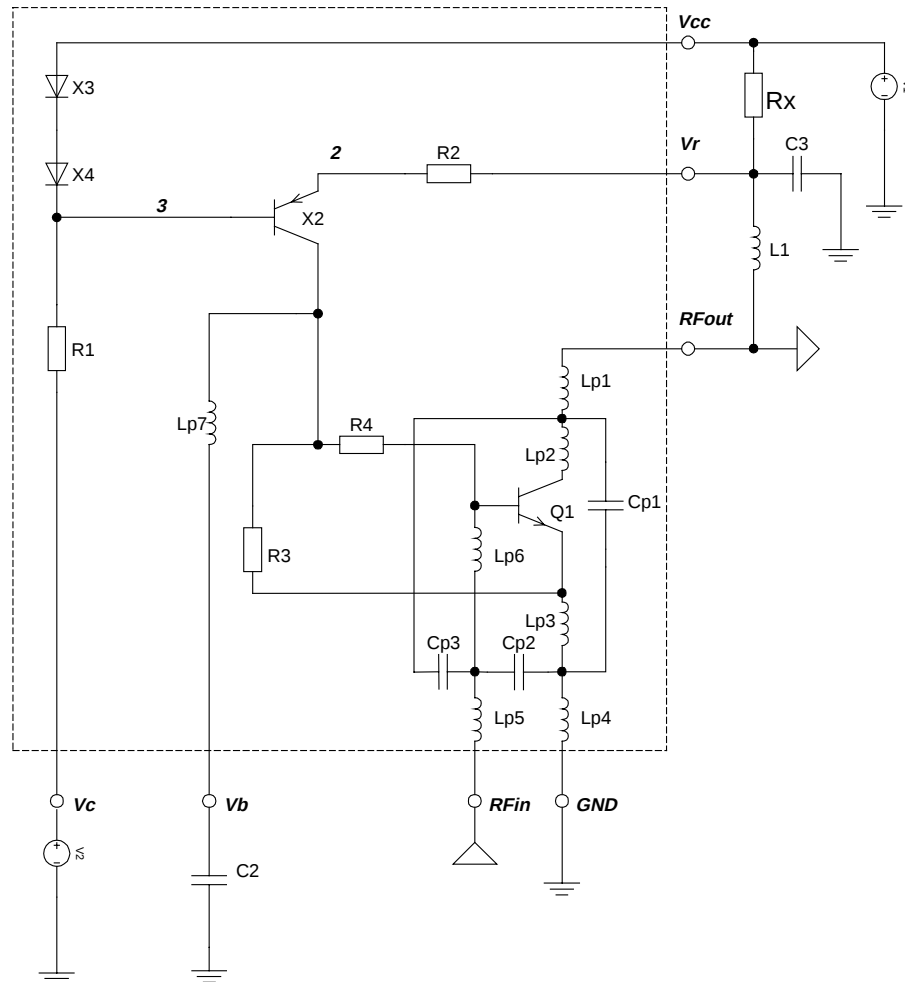
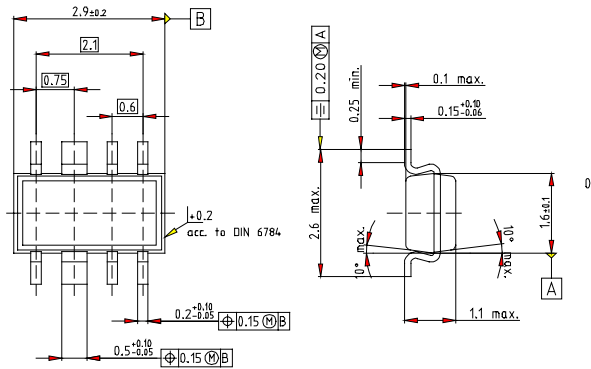


Figure 4. Parasitic circuit elements for frequencies above 100MHz

Element	Value
Lp1	0.58nH
Lp2	0.56nH
Lp3	0.23nH
Lp4	0.05nH
Lp5	0.53nH
Lp6	0.47nH
Lp7	1nH
Cp1	134fF
Cp2	136fF
Cp3	6.9fF

Table 1. Parasitic circuit elements for frequencies above 100MHz

Package



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